

QS5K2

Transistors

# 2.5V Drive Nch+Nch MOS FET

## QS5K2

### ●Structure

Silicon N-channel MOS FET

### ●Features

- 1) Low On-resistance.
- 3) Space saving, small surface mount package (TSMT5).

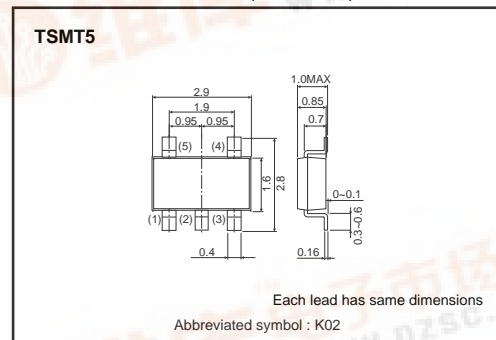
### ●Applications

Switching

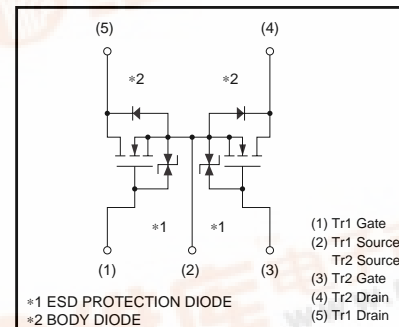
### ●Packaging specifications

Type	Package	Taping
	Code	TR
	Basic ordering unit (pieces)	3000
QS5K2		○

### ●External dimensions (Unit : mm)



### ●Inner circuit



### ●Absolute maximum ratings (Ta=25°C)

&lt;It is the same ratings for the Tr1 and Tr2&gt;

Parameter	Symbol	Limits	Unit
Drain-source voltage	$V_{DS}$	30	V
Gate-source voltage	$V_{GS}$	12	V
Drain current	Continuous	$I_D$	$\pm 2.0$ A
	Pulsed	$I_{DP}$ *1	$\pm 8.0$ A
Source current (Body diode)	Continuous	$I_S$	0.8 A
	Pulsed	$I_{SP}$ *1	3.2 A
Total power dissipation	$P_D$ *2	1.25	W / TOTAL
		0.9	W / ELEMENT
Channel temperature	$T_{ch}$	150	°C
Range of storage temperature	$T_{stg}$	-55 to +150	°C

\*1  $P_w \leq 10 \mu s$ , Duty cycle  $\leq 1\%$ 

\*2 Mounted on a ceramic board

### ●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	$R_{th(ch-a)}$ *	100	°C/W
		139	°C/W

\* Mounted on a ceramic board

## Transistors

## ●Electrical characteristics (Ta=25°C)

&lt;It is the same characteristics for the Tr1 and Tr2&gt;

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I <sub>GSS</sub>	—	—	10	μA	V <sub>GS</sub> =12V, V <sub>DS</sub> =0V
Drain-source breakdown voltage	V <sub>(BR) DSS</sub>	30	—	—	V	I <sub>D</sub> = 1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> =0V
Gate threshold voltage	V <sub>GS (th)</sub>	0.5	—	1.5	V	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA
Static drain-source on-state resistance	R <sub>DS (on)</sub> *	—	71	100	mΩ	I <sub>D</sub> = 2A, V <sub>GS</sub> = 4.5V
		—	76	107	mΩ	I <sub>D</sub> = 2A, V <sub>GS</sub> = 4.0V
		—	110	154	mΩ	I <sub>D</sub> = 2A, V <sub>GS</sub> = 2.5V
Forward transfer admittance	Y <sub>fs</sub>   *	1.5	—	—	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 2A
Input capacitance	C <sub>iss</sub>	—	175	—	pF	V <sub>DS</sub> = 10V
Output capacitance	C <sub>oss</sub>	—	50	—	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	C <sub>rss</sub>	—	25	—	pF	f=1MHz
Turn-on delay time	t <sub>d (on)</sub> *	—	8	—	ns	V <sub>DD</sub> ≐ 15V
Rise time	t <sub>r</sub> *	—	10	—	ns	I <sub>D</sub> = 1A
Turn-off delay time	t <sub>d (off)</sub> *	—	21	—	ns	V <sub>GS</sub> = 4.5V
Fall time	t <sub>f</sub> *	—	8	—	ns	R <sub>L</sub> = 15Ω
Total gate charge	Q <sub>g</sub> *	—	2.8	3.9	nC	R <sub>G</sub> =10Ω
Gate-source charge	Q <sub>gs</sub> *	—	0.6	—	nC	V <sub>DD</sub> ≐ 15V
Gate-drain charge	Q <sub>gd</sub> *	—	0.8	—	nC	V <sub>GS</sub> = 4.5V
						I <sub>D</sub> = 2A

\*Pulsed

## ●Body diode characteristics (Source-drain) (Ta=25°C)

&lt;It is the same characteristics for the Tr1 and Tr2&gt;

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V <sub>SD</sub> *	—	—	1.2	V	I <sub>S</sub> = 3.2A, V <sub>GS</sub> =0V

\* Pulsed

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